

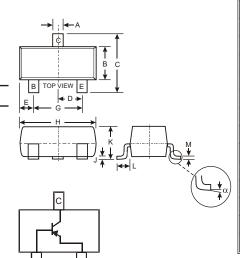
### PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

#### **Features**

- Epitaxial Planar Die Construction
- Complementary NPN Type Available
- (MMBT3904)
- Ideal for Medium Power Amplification and Switching
- Also Available in Lead Free Version

#### **Mechanical Data**

- Case: SOT-23, Molded Plastic
- Case material UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish). Please see Ordering Information, Note 4, on Page 2
- Terminal Connections: See Diagram
- Marking (See Page 2): K3N
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approx.)



	SOT-23								
Dim	Min	Max							
Α	0.37	0.51							
В	1.20	1.40							
С	2.30	2.50							
D	0.89	1.03							
E	0.45	0.60							
G	1.78	2.05							
Н	2.80	3.00							
J	0.013	0.10							
K	0.903	1.10							
L	0.45	0.61							
M	0.085	0.180							
α	0°	8°							
All Din	nensions	in mm							

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## **Maximum Ratings** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	MMBT3906	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current - Continuous (Note 1)	Ic	-200	mA
Power Dissipation (Note 1)	P <sub>d</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	417	°C/W
Operating and Storage and Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



# Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-40	_	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-40	_	V	I <sub>C</sub> = -1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5.0	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	I <sub>CEX</sub>	_	-50	nA	$V_{CE} = -30V$ , $V_{EB(OFF)} = -3.0V$
Collector Cutoff Current	Ісво	_	-50	nA	$V_{CB} = -30V, I_{E} = 0$
Base Cutoff Current	I <sub>BL</sub>	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
ON CHARACTERISTICS (Note 2)	•			•	
DC Current Gain	h <sub>FE</sub>	60 80 100 60 30	300 — —	_	$ \begin{array}{ c c c c c c c } \hline & I_C = -100\mu\text{A}, \ V_{CE} = -1.0V \\ I_C = -1.0\text{mA}, \ V_{CE} = -1.0V \\ I_C = -10\text{mA}, \ V_{CE} = -1.0V \\ I_C = -50\text{mA}, \ V_{CE} = -1.0V \\ I_C = -100\text{mA}, \ V_{CE} = -1.0V \\ \hline \end{array} $
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	-0.25 -0.40	V	$I_C = -10mA$ , $I_B = -1.0mA$ $I_C = -50mA$ , $I_B = -5.0mA$
Base- Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	-0.65	-0.85 -0.95	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
SMALL SIGNAL CHARACTERISTICS			•	•	
Output Capacitance	C <sub>obo</sub>	_	4.5	pF	$V_{CB} = -5.0V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	C <sub>ibo</sub>	_	10	pF	$V_{EB} = -0.5V$ , $f = 1.0MHz$ , $I_{C} = 0$
Input Impedance	h <sub>ie</sub>	2.0	12	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.1	10	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h <sub>fe</sub>	100	400	_	f = 1.0kHz
Output Admittance	h <sub>oe</sub>	3.0	60	μS	
Current Gain-Bandwidth Product	f⊤	250	_	MHz	V <sub>CE</sub> = -20V, I <sub>C</sub> = -10mA, f = 100MHz
Noise Figure	NF	_	4.0	dB	$V_{CE}$ = -5.0V, $I_{C}$ = -100 $\mu$ A, $R_{S}$ = 1.0k $\Omega$ , $f$ = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>d</sub>		35	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Rise Time	t <sub>r</sub>	_	35	ns	$V_{BE(off)} = 0.5V, I_{B1} = -1.0mA$
Storage Time	ts	_	225	ns	V <sub>CC</sub> = -3.0V, I <sub>C</sub> = -10mA,
Fall Time	t <sub>f</sub>	_	75	ns	$I_{B1} = I_{B2} = -1.0 \text{mA}$

# **Ordering Information** (Note 3)

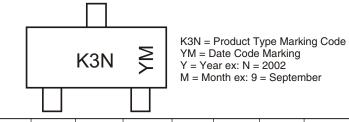
Device	Packaging	Shipping
MMBT3906 -7	SOT-23	3000/Tape & Reel

Notes:

Date Code Key

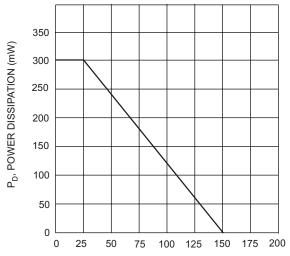
- 2. Short duration test pulse used to minimize self-heating effect.
- 3. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.
- For Lead Free version (with Lead Free terminal finish) part number, please add "-F" suffix to part number above. Example: MMBT3906-7-F.

## **Marking Information**

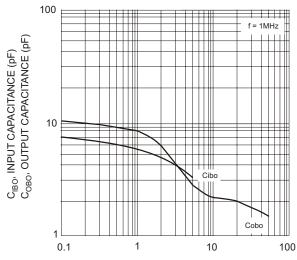


Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	М	N	Р	R	S	Т	U	V	W
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec





T<sub>A</sub>, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs Ambient Temperature



V<sub>CB</sub>, COLLECTOR-BASE VOLTAGE (V) Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

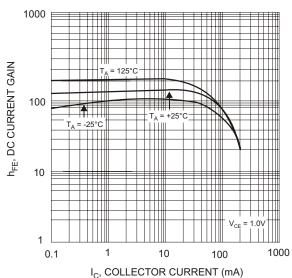


Fig. 3, Typical DC Current Gain vs Collector Current

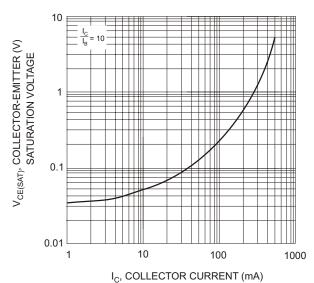
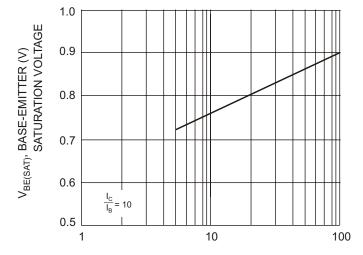


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current



I<sub>C</sub>, COLLECTOR CURRENT (mA) Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current